CLAIMS

1. A semiconductor structure, comprising:

a functional structure, a first mark structure and a second mark structure located on a substrate, wherein the functional structure, the first mark structure and the second mark structure have a same feature size;

a first dielectric layer located at the functional structure, the first mark structure and the second mark structure, wherein a thickness of the first dielectric layer at the functional structure is different from a thickness of the first dielectric layer at the first mark structure;

a second dielectric layer covering the first dielectric layer;

a third dielectric layer covering the second dielectric layer at the functional structure and not covering the second dielectric layer at the second mark structure.

2. The semiconductor structure of claim 1, wherein

the thickness of the first dielectric layer at the first mark structure is in a range of 250 nm to 350 nm; and

the thickness of the first dielectric layer at the functional structure is 50 nm to 100 nm smaller than the thickness of the first dielectric layer at the first mark structure.

3. The semiconductor structure of claim 1, wherein a total thickness of the first dielectric layer and the second dielectric layer at the functional structure is equal to a total thickness of the first dielectric layer and the second dielectric layer at the first mark structure.

4. The semiconductor structure of claim 1, wherein the functional structure and the first mark structure comprise a plurality of saw-toothed grooves, each of the grooves is filled with the

first dielectric layer, and a height of the first dielectric layer filling in each of the grooves of the functional structure is different from a height of the first dielectric layer filling in each of the grooves of the first mark structure.

5. The semiconductor structure of claim 4, wherein the height of the first dielectric layer filling in each of the grooves of the functional structure is smaller than the height of the first dielectric layer filling in each of the grooves of the first mark structure.

6. The semiconductor structure of claim 5, wherein the height of the first dielectric layer filling in each of the grooves of the first mark structure is equal to a depth of each of the grooves of the first mark structure.

7. The semiconductor structure of claim 1, further comprising:

a third mark structure located on the substrate, wherein the functional structure and the third mark structure have different feature sizes.

8. The semiconductor structure of claim 7, wherein a thickness of the first dielectric layer at the third mark structure is equal to the thickness of the first dielectric layer at the functional structure.

9. The semiconductor structure of claim 8, wherein a total thickness of the first dielectric layer and the second dielectric layer at the third mark structure is equal to the total thickness of the first dielectric layer and the second dielectric layer at the functional structure.

10. The semiconductor structure of claim 9, wherein the third dielectric layer at the third mark structure covers the second dielectric layer.

11. A method for manufacturing a semiconductor structure, comprising:

providing a substrate;

forming a functional structure, a first mark structure, a second mark structure and a third mark structure on the substrate, wherein the functional structure, the first mark structure and the second mark structure have a same feature size, and the third mark structure and the functional structure have different feature sizes; and

forming a first dielectric layer of which a thickness at the functional structure is different from a thickness at the first mark structure, wherein the first dielectric layer is further formed at the second mark structure and the third mark structure, a thickness of the first dielectric layer at the second mark structure is equal to the thickness of the first dielectric layer at the first mark structure, and a thickness of the first dielectric layer at the third mark structure is different from the thickness of the first dielectric layer at the second mark structure.

12. The method of claim 11, wherein the forming the first dielectric layer of which the thickness at the functional structure is different from the thickness at the first mark structure comprises:

forming the first dielectric layer on the substrate; and

forming a photoresist layer on the first dielectric layer, removing the photoresist layer at the functional structure by a manufacturing process, and removing part of the first dielectric layer from the functional structure by an etching process to form the first dielectric layer of which the thickness at the functional structure is smaller than the thickness at the first mark structure.

13. The method of claim 11, further comprising:

forming a second dielectric layer on the first dielectric layer, wherein sums of the

thickness of the first dielectric layer and a thickness of the second dielectric layer at the functional structure, at the first mark structure, at the second mark structure and at the third mark structure are equal.

14. The method of claim 13, further comprising:

forming a third dielectric layer covering the second dielectric layer at the functional structure and the third mark structure, and not forming the third dielectric layer covering the second dielectric layer at the second mark structure.

15. The method for manufacturing the semiconductor structure of claim 14, wherein the forming the third dielectric layer covering the second dielectric layer at the functional structure and the third mark structure, and not forming the third dielectric layer covering the second dielectric layer at the second mark structure comprises:

forming the third dielectric layer on the second dielectric layer at the functional structure, the third mark structure and the second mark structure; and

sequentially forming a mask layer and a photoresist layer on the third dielectric layer, removing the photoresist layer from the second mark structure by a manufacturing process, and removing the mask layer and the third dielectric layer from the second mark structure by an etching process to form the third dielectric layer covering the second dielectric layer at the functional structure and the third mark structure but not covering the second dielectric layer at the second mark structure.